

650 V Power SiC Gen 3 Merged PIN Schottky Diode, 10 A



FEATURES

- Majority carrier diode using Schottky technology on SiC wide band gap material
- Improved V_F and efficiency by thin wafer technology
- Positive V_F temperature coefficient for easy paralleling
- Virtually no recovery tail and no switching losses
- Temperature invariant switching behavior
- 175 °C maximum operating junction temperature
- MPS structure for high ruggedness to forward current surge events
- Meets JESD 201 class 2 whisker test
- Solder bath temperature 275 °C maximum, 10 s per JESD 22-B106
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE

LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS	
$I_{F(AV)}$	10 A
V_R	650 V
V_F at I_F at 150 °C	1.46 V
T_J max.	175 °C
I_R at V_R at 175 °C	4.5 μ A
Q_C ($V_R = 400$ V)	29 nC
Package	TO-220AC 2L
Circuit configuration	Single

DESCRIPTION / APPLICATIONS

Wide band gap SiC based 650 V Schottky diode, designed for high performance and ruggedness.

Optimum choice for high speed hard switching and efficient operation over a wide temperature range, it is also recommended for all applications suffering from Silicon ultrafast recovery behavior.

Typical applications include AC/DC PFC and DC/DC ultra high frequency output rectification in FBPS and LLC converters.

MECHANICAL DATA

Case: TO-220AC 2L

Molding compound meets UL 94 V-0 flammability rating
Base P/N-M3 - halogen-free, RoHS-compliant

Terminals: matte tin plated leads, solderable per J-STD-002 and JESD 22-B102

Mounting torque: 10 in-lbs maximum

ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C unless otherwise specified)				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Peak repetitive reverse voltage	V_{RRM}		650	V
Average rectified forward current	$I_{F(AV)}$	$T_C = 130$ °C (DC)	10	A
DC blocking voltage	V_{DC}		650	V
Repetitive peak forward current	I_{FRM}	$T_C = 25$ °C, $f = 50$ Hz, square wave, DC = 25 %	41	A
Non-repetitive peak forward surge current	I_{FSM}	$T_C = 25$ °C, $t_p = 10$ ms, half sine wave	60	A
		$T_C = 110$ °C, $t_p = 10$ ms, half sine wave	58	
Power dissipation	$P_{tot}^{(1)}$	$T_C = 25$ °C	64	W
		$T_C = 110$ °C	28	
I^2t value	$\int i^2 dt$	$T_C = 25$ °C	18	A ² s
		$T_C = 110$ °C	17	
Operating junction and storage temperatures	$T_J^{(2)}, T_{Stg}$		-55 to +175	°C

Notes

(1) Based on maximum R_{th}

(2) The heat generated must be less than the thermal conductivity from junction-to-ambient: $dP_D/dT_J < 1/R_{\theta JA}$



ELECTRICAL SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$ unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Forward voltage	V_F	$I_F = 10\text{ A}$	-	1.3	1.5	V
		$I_F = 10\text{ A}, T_J = 150\text{ }^\circ\text{C}$	-	1.46	1.85	
		$I_F = 10\text{ A}, T_J = 175\text{ }^\circ\text{C}$	-	1.52	-	
Reverse leakage current	I_R	$V_R = V_R\text{ rated}$	-	0.7	55	μA
		$V_R = V_R\text{ rated}, T_J = 150\text{ }^\circ\text{C}$	-	2.8	125	
		$V_R = V_R\text{ rated}, T_J = 175\text{ }^\circ\text{C}$	-	4.5	-	
Total capacitance	C	$V_R = 1\text{ V}, f = 1\text{ MHz}$	-	445	-	pF
		$V_R = 400\text{ V}, f = 1\text{ MHz}$	-	43	-	
Total capacitive charge	Q_C	$V_R = 400\text{ V}, f = 1\text{ MHz}$	-	29	-	nC

THERMAL - MECHANICAL SPECIFICATIONS ($T_A = 25\text{ }^\circ\text{C}$ unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Thermal resistance, junction-to-case	R_{thJC}		-	1.8	2.3	$^\circ\text{C/W}$
Marking device			3C10ET07T			

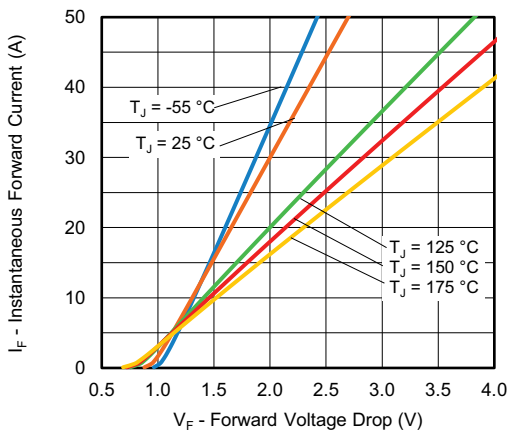


Fig. 1 - Typical Forward Voltage Drop Characteristics

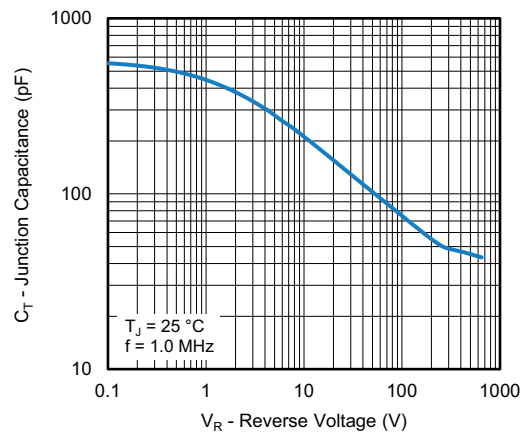


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

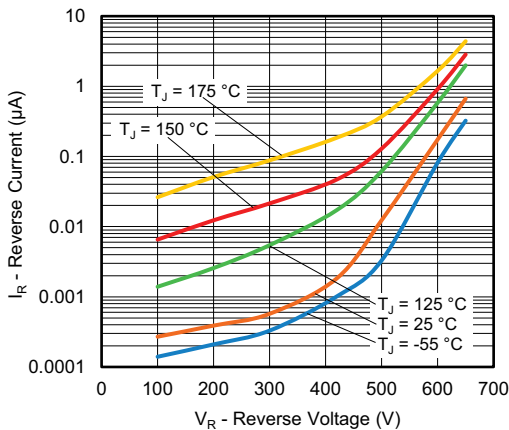


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

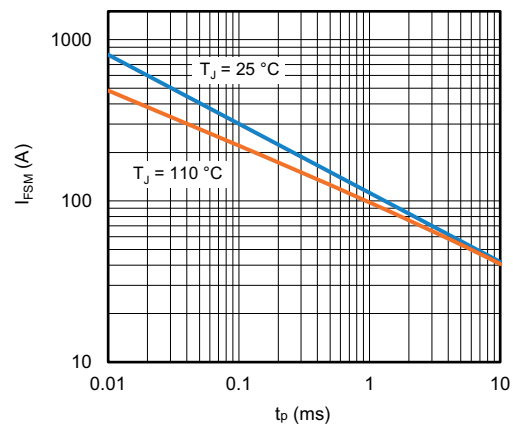


Fig. 4 - Non-Repetitive Peak Forward Surge Current vs. Pulse Duration (Square Wave)

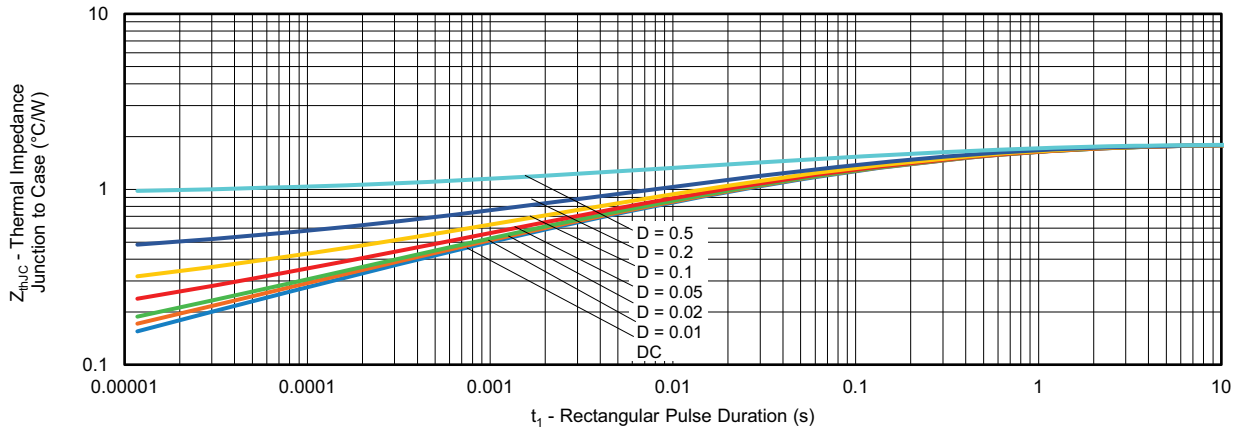


Fig. 5 - Typical Thermal Impedance Z_{thJC} Characteristics

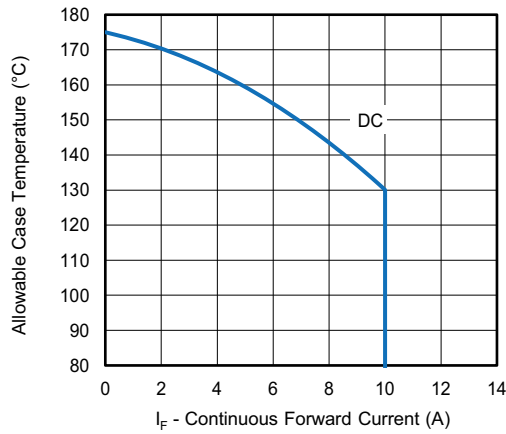


Fig. 6 - Maximum Allowable Case Temperature vs. Average Forward Current

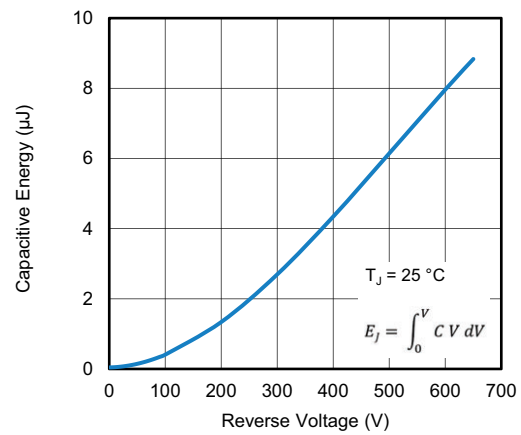


Fig. 8 - Typical Capacitive Energy vs. Reverse Voltage

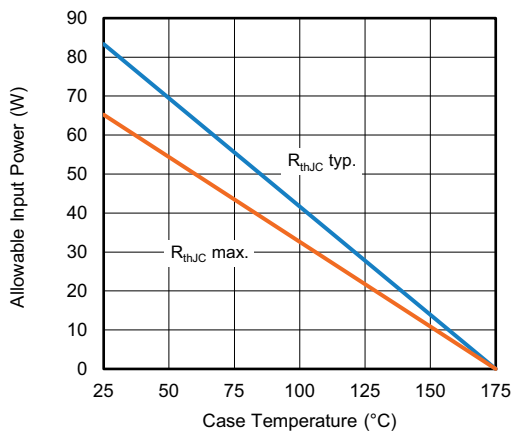


Fig. 7 - Forward Power Loss Characteristics

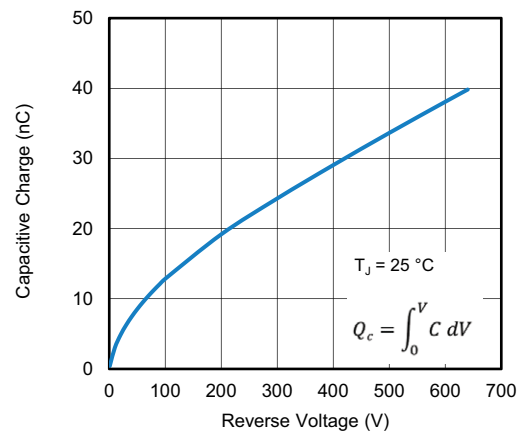
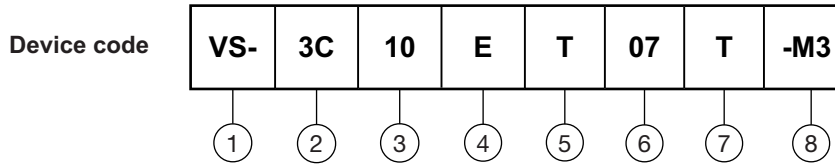


Fig. 9 - Typical Capacitive Charge vs. Reverse Voltage



ORDERING INFORMATION TABLE



- 1** - Vishay Semiconductors product
- 2** - 3C = SiC diode, Generation 3
- 3** - Current rating (10 = 10 A)
- 4** - E = single diode
- 5** - Package TO-220
- 6** - Voltage rating: (07 = 650 V)
- 7** - T = true 2 pin
- 8** - Environmental digit:
-M3 = halogen-free, RoHS-compliant, and termination lead (Pb)-free

ORDERING INFORMATION		
PREFERRED P/N	BASE QUANTITY	PACKAGING DESCRIPTION
VS-3C10ET07T-M3	50/tube	Antistatic plastic tubes

LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?96069
Part marking information	www.vishay.com/doc?95391



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